FTD36N06NA

N-Channel MOSFET

Lead Free Package and Finish

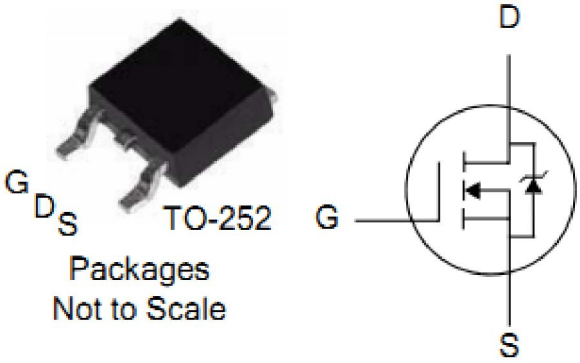
Applications:

- Power switch circuit of adaptor and charger;
- LED backlight driver;
- Synchronous rectification

V_{DSS}	$R_{DS(ON)}$(Typ.)	I_D
60V	23mΩ	25A

Features:

- Fast Switching
- Low ON Resistance
- Low Gate Charge
- Low Reverse transfer capacitances
- 100% Single Pulse avalanche energy Test



Ordering Information

PART NUMBER	PACKAGE	BRAND
FTD36N06NA	TO-252	***IPS***

Absolute Maximum Ratings

T_J=25℃ unless otherwise specified

Symbol	Parameter	FTD36N06NA	Units
V_{DSS}	Drain-to-Source Voltage	60	V
I_D	Continuous Drain Current T_C = 25 °C	25	A
	Continuous Drain Current T_C =100℃	17.5	A
I_{DM}	Pulsed Drain Current T_C = 25 °C (NOTE *1)	100	A
V_{GS}	Gate-to-Source Voltage	±20	V
E_{AS}	Single Pulse Avalanche Energy(NOTE *2)	56.2	mJ
P_D	Power Dissipation T_C = 25 °C	36.2	W
T_J and T_{STG}	Operating Junction and Storage Temperature Range	150，-55 to150	℃

Thermal Resistance

Symbol	Parameter	Max.	Units	Test Conditions
$R_{\theta JC}$	Junction-to-Case	3.45	℃/W	Water cooled heatsink, P_D adjusted for a peak junction temperature of +150℃.
$R_{\theta JA}$	Junction-to-Ambient	111.5		1 cubic foot chamber, free air.

OFF Characteristics T_J=25℃ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	60	--	--	V	V_{GS}=0V, I_D=250μA
I_{DSS}	Drain-to-Source Leakage Current	--	--	1	μA	V_{DS}=60V, V_{GS}=0V T_J=25℃
		--	--	100		V_{DS}=48V, V_{GS}=0V T_J=125℃
I_{GSS}	Gate-to-Source Forward Leakage	--	--	+100	nA	V_{GS}=+20V
	Gate-to-Source Reverse Leakage	--	--	-100		V_{GS}= -20V

ON Characteristics T_J=25℃ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
$R_{DS(ON)}$	StaticDrain-to-Source On-Resistance	--	23	29	mΩ	V_{GS}=10V, I_D=19A
		--	30	38	mΩ	V_{GS}=4.5V, I_D=19A
$V_{GS(TH)}$	Gate Threshold Voltage	1	1.5	2	V	V_{DS}=V_{GS},I_D=250μA
Pulse width ≤300μs; duty cycle≤ 2%						

Dynamic Characteristics Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
R_g	Gate resistance	--	1.9	--	Ω	f =1.0MHz
C_{iss}	Input Capacitance	--	939	--	pF	V_{GS}= 0V,V_{DS} = 30V f =1.0MHz
C_{oss}	Output Capacitance	--	73.5	--		
C_{rss}	Reverse Transfer Capacitance	--	52.7	--		
Q_g	Total Gate Charge	--	21.2	--	nC	I_D=20A,V_{DD}=30V V_{GS} = 10V
Q_{gs}	Gate-to-Source Charge	--	3.6	--		
Q_{gd}	Gate-to-Drain (“Miller”) Charge	--	5.5	--		

Resistive Switching Characteristics Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
$t_{d(ON)}$	Turn-on Delay Time	--	8.4	--	ns	V_{DD}=30V, I_D=20A, V_{GS}=10V R_G=3Ω
t_{rise}	Rise Time	--	8.5	--		
$t_{d(OFF)}$	Turn-Off Delay Time	--	35.4	--		
t_{fall}	Fall Time	--	4.8	--		

Source-Drain Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I_S	Continuous Source Current (Body Diode)	--	--	25	A	T_C=25℃
I_{SM}	Maximum Pulsed Current (Body Diode)	--	--	100	A	
V_{SD}	Diode Forward Voltage	--	--	1.2	V	I_{SD}=20A, V_{GS}=0V
t_{rr}	Reverse Recovery Time	--	18.8	--	ns	di/dt=100A/us
Q_{rr}	Reverse Recovery Charge	--	13.4	--	nC	IF=20A
Pulse width ≤300μs; duty cycle ≤ 2%						

Notes:

*1. Repetitive rating; pulse width limited by maximum junction temperature.

*2. L=0.5mH,V_{DD}=30V,Ias=15A Start T_J=25℃

*3. Recommend soldering temperature defined by IPC/JEDEC J-STD 020

Characteristics Curve：

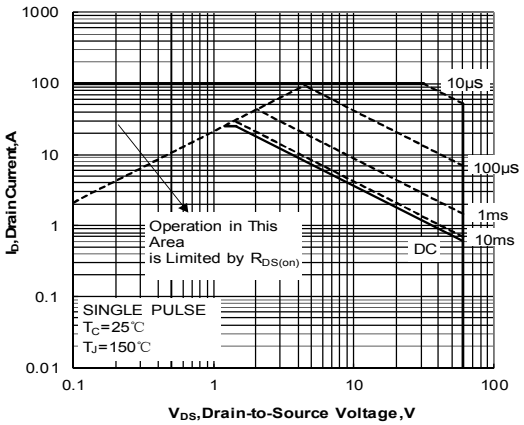


Figure 1 . Maximum Safe Operating Area

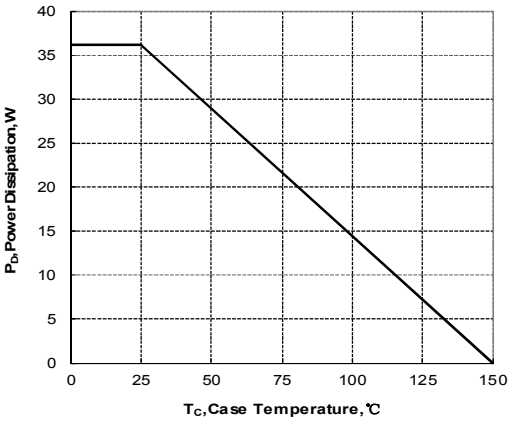


Figure 2. Maximum Power Dissipation vs Case Temperature

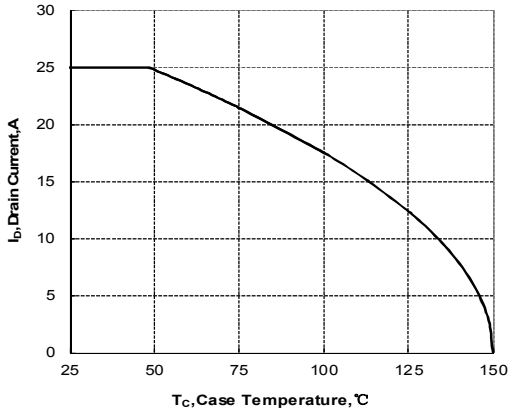


Figure 3. Maximum Continuous Drain Current vs Case Temperature

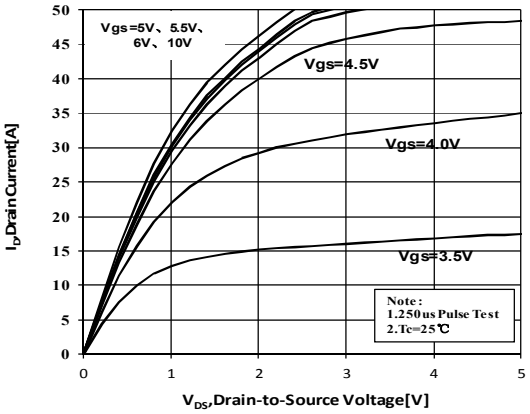


Figure 4. Typical output Characteristics

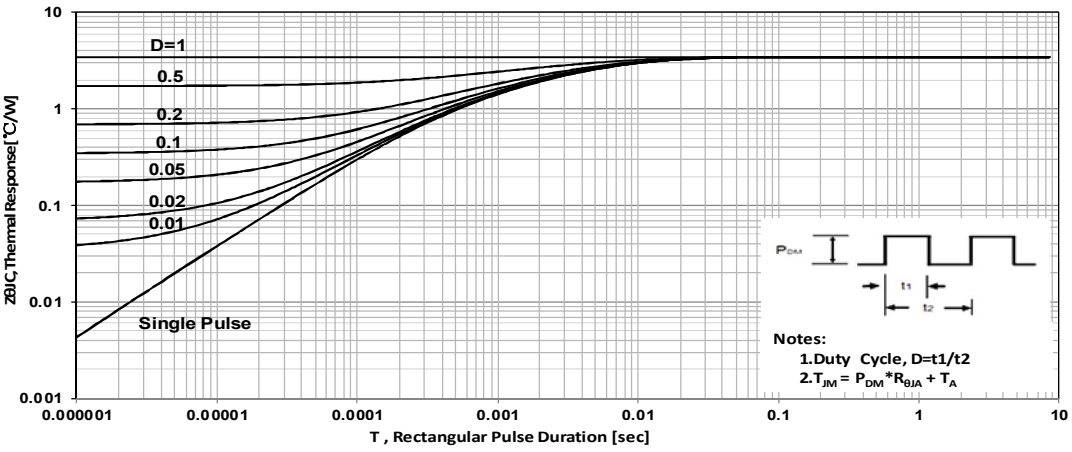


Figure 5 Maximum Effective Thermal Impedance , Junction to Case

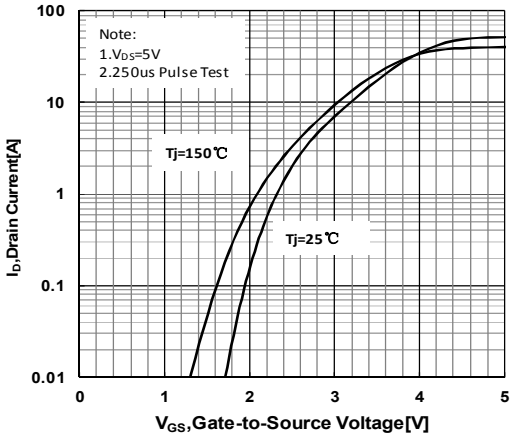


Figure 6 Typical Transfer Characteristics

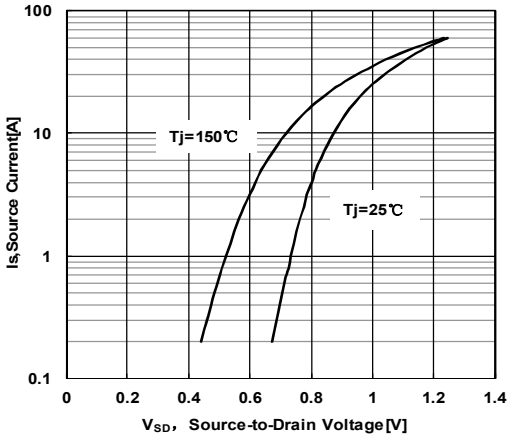


Figure 7 Typical Body Diode Transfer Characteristics

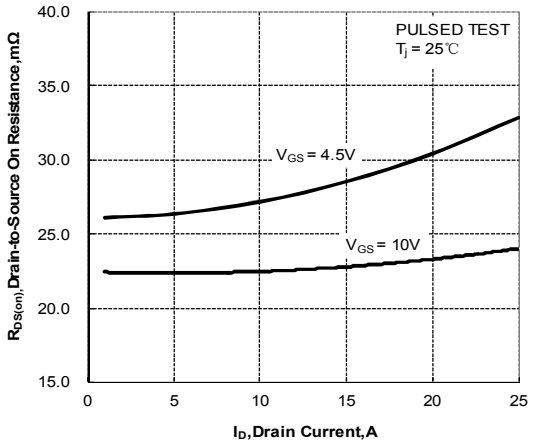


Figure 8. Drain-to-Source On Resistance vs Drain Current

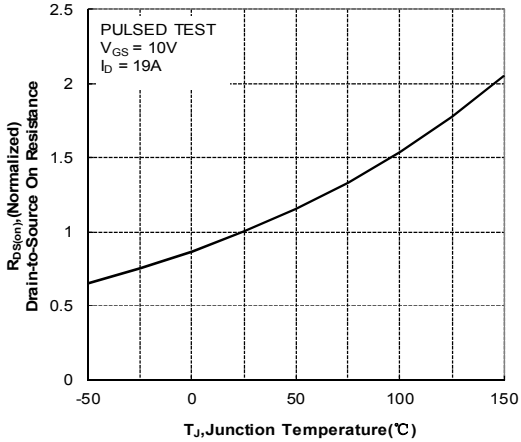


Figure 9. Normalized On Resistance vs Junction Temperature

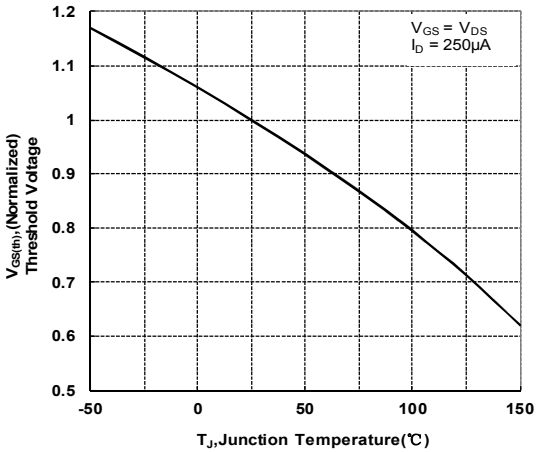


Figure10. Normalized Threshold Voltage vs Junction Temperature

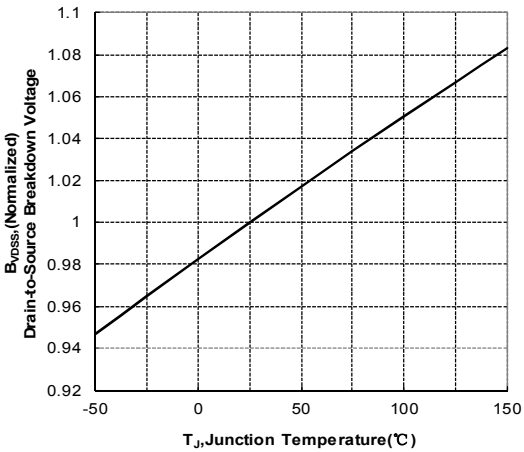


Figure 11. Normalized Breakdown Voltage vs Junction Temperature

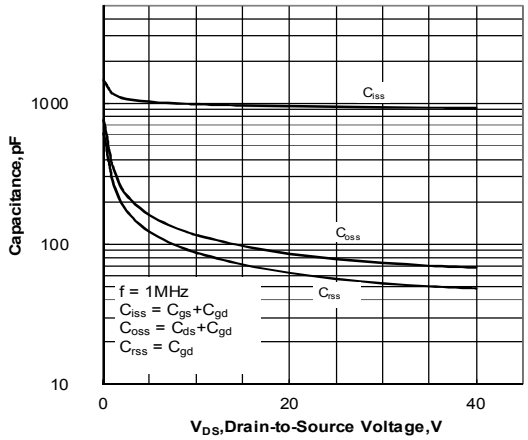


Figure 12. Capacitance Characteristics

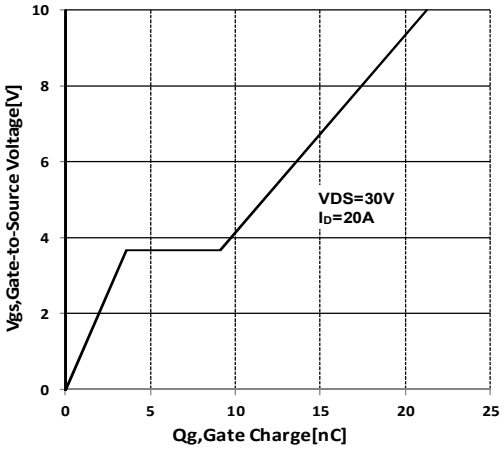


Figure 13 Typical Gate Charge vs Gate to Source Voltage

Test Circuits and Waveforms

Figure 14. Gate Charge Test Circuit

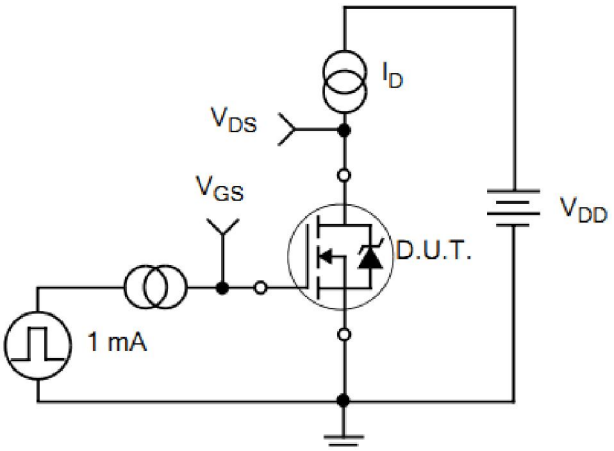


Figure 15. Gate Charge Waveforms

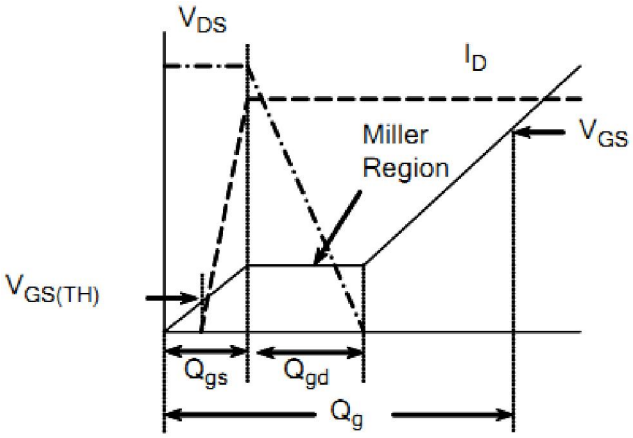


Figure 16. Resistive Switching Test Circuit

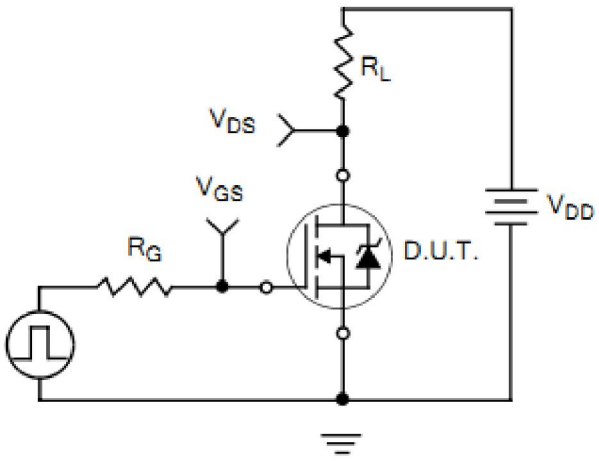


Figure 17. Resistive Switching Waveforms

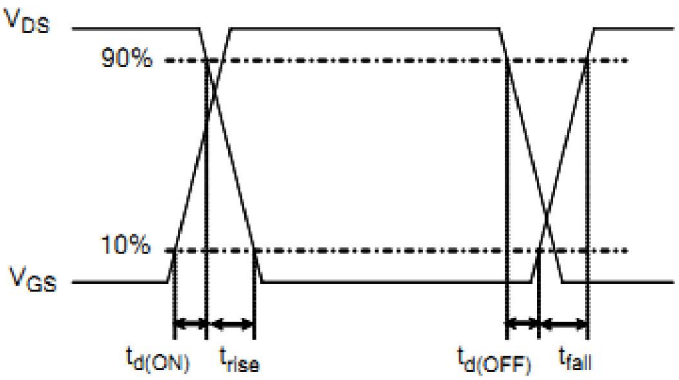


Figure 18. Diode Reverse Recovery Test Circuit

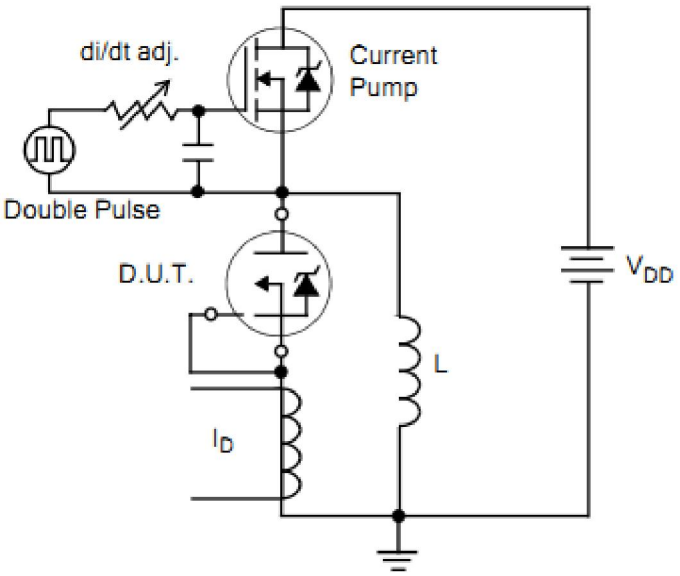


Figure 19. Diode Reverse Recovery Waveform

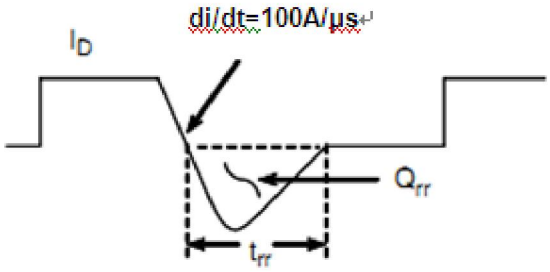


Figure20.Unclamped Inductive Switching Test Circuit

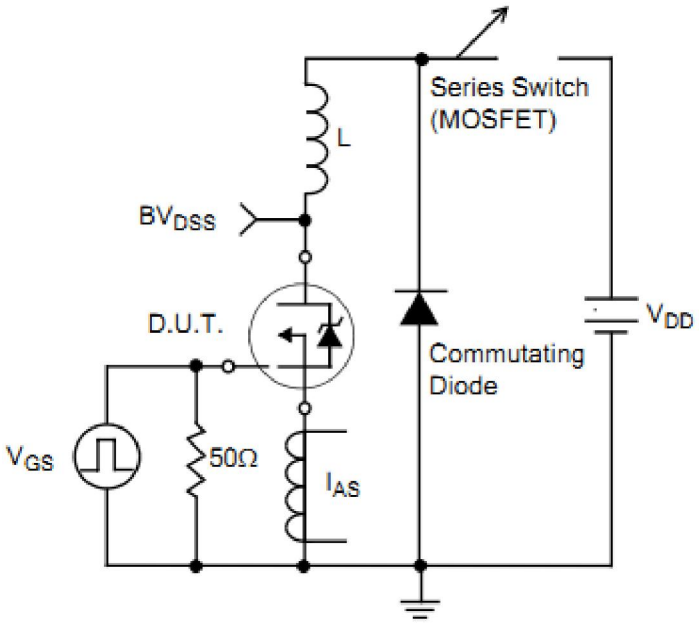
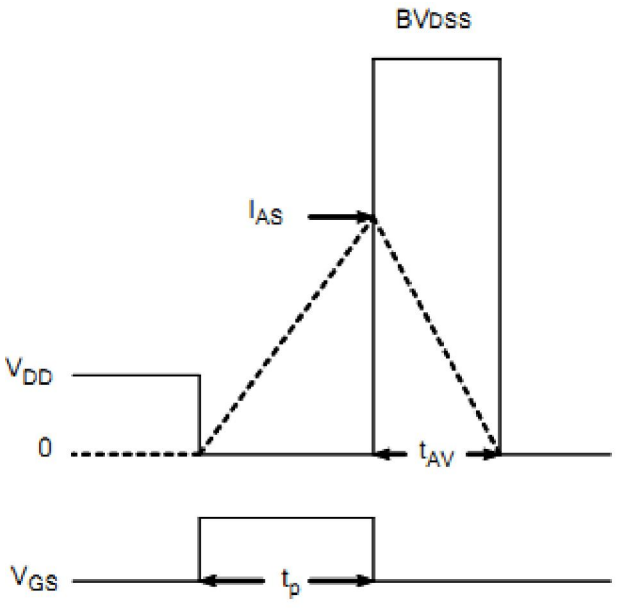


Figure21.Unclamped Inductive Switching Waveform



$$E_{AS} \quad \frac{I_{AS}^{2} L}{2}$$

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